Product data sheet

1. General description

Hyperfast power diode in a SOD113A (2-lead TO-220-F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- · High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; Fig. 1; Fig. 2		-	-	20	A
Static charact	eristics						
V _F	forward voltage	I _F = 20 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.2	1.97	V
Dynamic char	Dynamic characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 6		-	16	20	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113A)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYC20DX-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220F "full pack"	SOD113A		

7. Marking

Table 4. Marking codes

Type number	Marking code
BYC20DX-600P	BYC20DX-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; Fig. 1; Fig. 2	-	20	Α
I _{FRM}	repetitive peak forward current	δ = 0.5; t_p = 25 μ s; square-wave pulse	-	40	Α

BYC20DX-600P

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Symbol	Parameter	Conditions	Min	Max	Unit
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	-	250	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	275	А
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

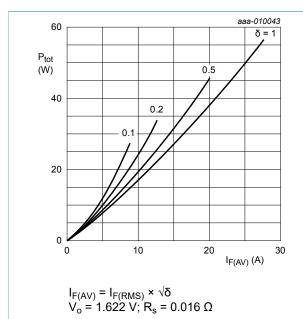
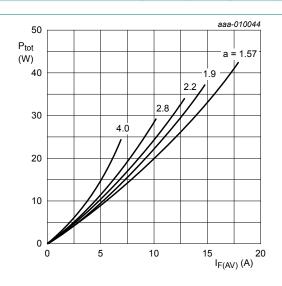


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}$ / $I_{F(AV)}$ V_o = 1.622 V; R_s = 0.016 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

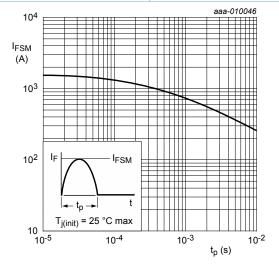
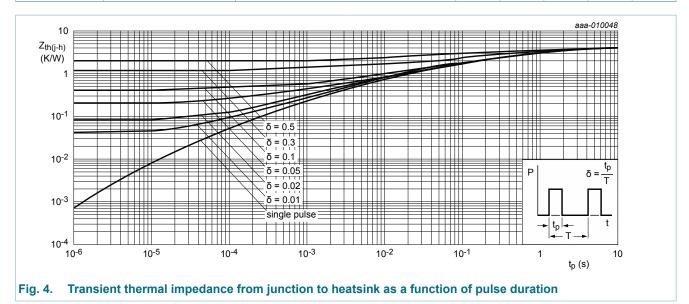


Fig. 3. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 4	-	-	4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



10. Isolation characteristics

Table 7. Isolation characteristics

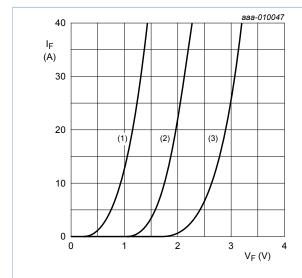
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink	_	10	-	pF

11. Characteristics

Table 8. Characteristics

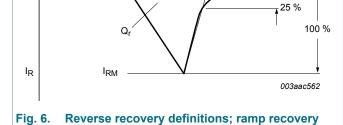
Table 6. Sharacteriotics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics							
V _F	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 5</u>		-	2	2.9	V
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I _F = 20 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.2	1.97	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	1	mA
Dynamic cl	haracteristics			'	'	
Q _r I	recovered charge	$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 6$	-	47	-	nC
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 6$	-	193	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$	-	16	20	ns
		$I_F = 20 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 6$	-	26	-	ns
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 25 \text{ °C}; Fig. 6$	-	33	-	ns
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 °C; Fig. 6$	-	51	-	ns
I _{RM}	peak reverse recovery current	$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 25 \text{ °C}; Fig. 6$	-	2.8	-	A
		$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 6$	-	7.6	-	A



 V_o = 1.622 V; R_s = 0.016 Ω (1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_i = 25$ °C; maximum values



 dI_F

dt

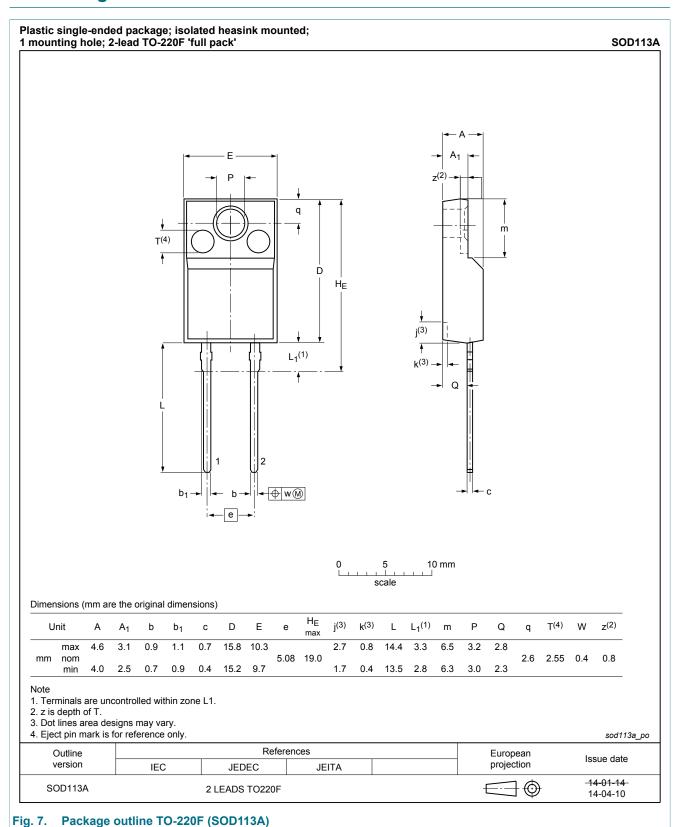
Fig. 5. Forward current as a function of forward voltage

time

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12. Package outline

BYC20DX-600P



13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Dual ultrafast power diode

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